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November 2013

FQB11N40C

N-Channel QFET® MOSFET

400 V, 10.5 A, 530 mΩ

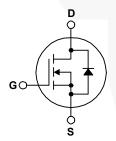
Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize onstate resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction, electronic lamp ballasts based on half bridge topology.

Features

- 10.5 A, 400V, $R_{DS(on)}$ = 530 m Ω (Max.) @ V_{GS} = 10 V, I_D = 5.25 A
- Low Gate Charge (Typ. 28 nC)
- Low Crss (Typ. 85 pF)
- · 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

| Symbol | Parameter | FQB11N40CTM | Unit | |
|-----------------------------------|--|-------------|------|--|
| V _{DSS} | Drain-Source Voltage | 400 | V | |
| I _D | Drain Current - Continuous (T _C = 25°C) | 10.5 | Α | |
| | - Continuous (T _C = 100°C) | 6.6 | Α | |
| I _{DM} | Drain Current - Pulsed (No | ote 1) 42 | A | |
| V _{GSS} | Gate-Source Voltage | ± 30 | V | |
| E _{AS} | Single Pulsed Avalanche Energy (No | ote 2) 360 | mJ | |
| I _{AR} | Avalanche Current (No | ote 1) 11 | Α | |
| E _{AR} | Repetitive Avalanche Energy (No. | ote 1) 13.5 | mJ | |
| dv/dt | Peak Diode Recovery dv/dt (No | ote 3) 4.5 | V/ns | |
| P_{D} | Power Dissipation (T _C = 25°C) | 135 | W | |
| | - Derate above 25°C | 1.07 | W/°C | |
| T _J , T _{STG} | Operating and Storage Temperature Range | -55 to +150 | °C | |
| T _L | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds | 300 | °C | |

Thermal Characteristics

| Symbol | Parameter | FQB11N40CTM | Unit | |
|-----------------|--|-------------|------|--|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max. 0.93 | | | |
| | Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max. | 62.5 | °C/W | |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (*1 in² pad of 2 oz copper), Max. | 40 | | |

Package Marking and Ordering Information

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|-----------|---------------------|----------------|-----------|------------|-----------|
| FQB11N40CTM | FQB11N40C | D ² -PAK | Tape and Reel | 330 mm | 24 mm | 800 units |

Electrical Characteristics T_C = 25°C unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Unit |
|---|---|---|-----|------|------|------|
| Off Cha | aracteristics | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | 400 | | | V |
| ΔBV _{DSS} / ΔT _J | Breakdown Voltage Temperature Coefficient | I _D = 250 μA, Referenced to 25°C | | 0.54 | | V/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 400 V, V _{GS} = 0 V | | - | 1 | μΑ |
| | | V _{DS} = 320 V, T _C = 125°C | | - | 10 | μΑ |
| I _{GSSF} | Gate-Body Leakage Current, Forward | V _{GS} = 30 V, V _{DS} = 0 V | | - | 100 | nA |
| I _{GSSR} | Gate-Body Leakage Current, Reverse | V _{GS} = -30 V, V _{DS} = 0 V | | | -100 | nA |
| On Cha | racteristics | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$ | 2.0 | | 4.0 | V |
| R _{DS(on)} | Static Drain-Source On-Resistance | V _{GS} = 10 V, I _D = 5.25 A | | 0.5 | 0.53 | Ω |
| 9 _{FS} | Forward Transconductance | V _{DS} = 40 V, I _D = 5.25 A | | 7.1 | | S |
| | ic Characteristics | | | | | |
| C _{iss} | Input Capacitance | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ | | 840 | 1090 | pF |
| C _{oss} | Output Capacitance | f = 1.0 MHz | | 250 | 325 | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 85 | 110 | pF |
| Switchi | ing Characteristics | | | | | |
| t _{d(on)} | Turn-On Delay Time | V _{DD} = 200 V, I _D = 10.5 A, | | 14 | 40 | ns |
| t _r | Turn-On Rise Time | $R_G = 25 \Omega$ | | 89 | 190 | ns |
| t _{d(off)} | Turn-Off Delay Time | - 1.6 | | 81 | 170 | ns |
| t _f | Turn-Off Fall Time | (Note 4) | | 81 | 170 | ns |
| Qg | Total Gate Charge | V _{DS} = 320 V, I _D = 10.5 A, | | 28 | 35 | nC |
| Q _{gs} | Gate-Source Charge | V _{GS} = 10 V | / | 4 | | nC |
| Q _{gd} | Gate-Drain Charge | (Note 4) | - | 15 | | nC |
| Drain-S | ource Diode Characteristics a | nd Maximum Ratings | | | | |
| I _S | Maximum Continuous Drain-Source Diode Forward Current | | | | 10.5 | Α |
| I_{SM} | Maximum Pulsed Drain-Source Diode Forward Current | | | | 42 | Α |
| V _{SD} | Drain-Source Diode Forward Voltage | V _{GS} = 0 V, I _S = 10.5 A | | - | 1.4 | V |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0 V, I _S = 10.5 A, | | 290 | // | ns |
| Q _{rr} | Reverse Recovery Charge | dI _F / dt = 100 A/μs | | 2.4 | | μС |

- Notes:
 1. Repetitive rating: pulse-width limited by maximum junction temperature.
 2. L = 5.7 mH, I_{AS} = 10.5 A, V_{DD} = 50 V, R_{C} = 25 Ω , starting T_{J} = 25°C.
 3. I_{SD} ≤ 10.5 A, di/dt ≤ 200 A/ μ s, V_{DD} ≤ BV $_{DSS}$, starting T_{J} = 25°C.
 4. Essentially independent of operating temperature.

Typical Characteristics

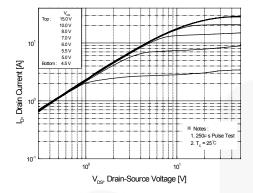


Figure 1. On-Region Characteristics

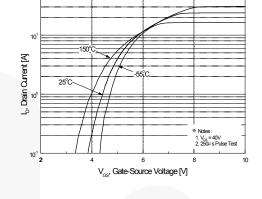


Figure 2. Transfer Characteristics

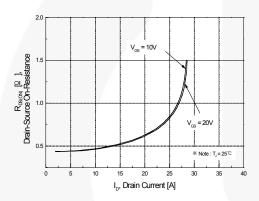


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

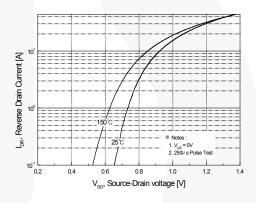


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

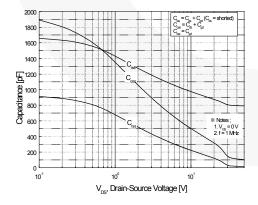


Figure 5. Capacitance Characteristics

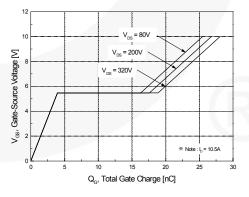


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

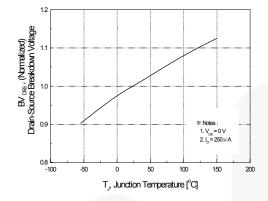
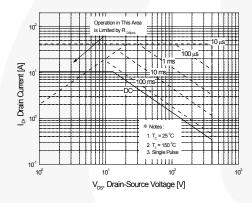


Figure 7. Breakdown Voltage Variation vs Temperature

Figure 8. On-Resistance Variation vs Temperature



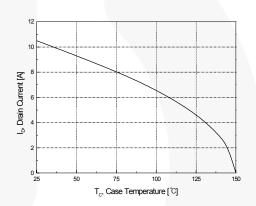


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs Case Temperature

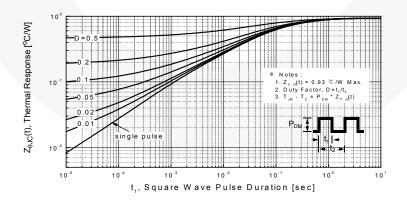


Figure 11. Transient Thermal Response Curve

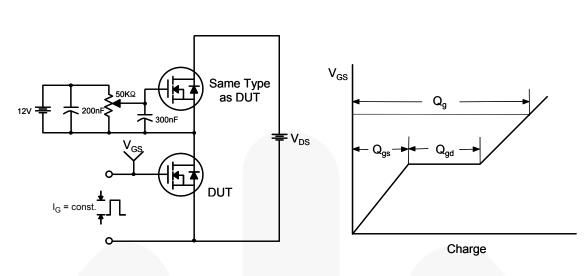


Figure 12. Gate Charge Test Circuit & Waveform

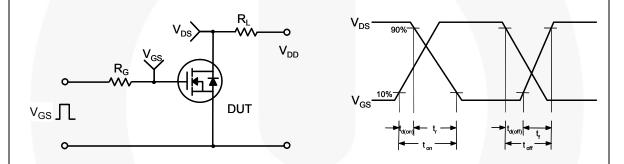


Figure 13. Resistive Switching Test Circuit & Waveforms

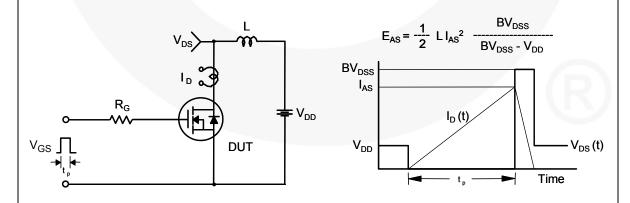
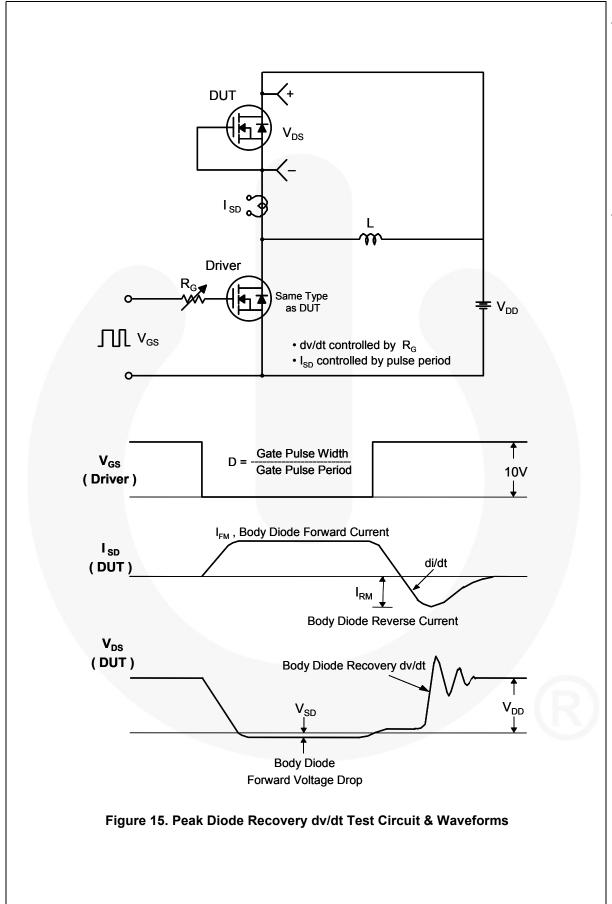


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

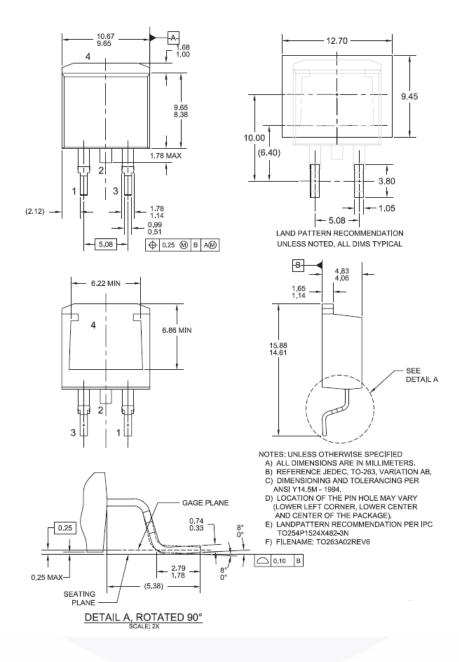


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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